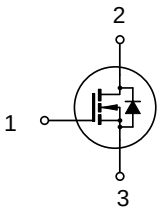
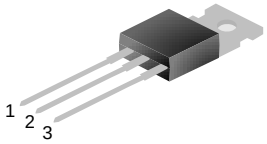
17A, 55V N-CHANNEL MOSFET

GENERAL DESCRIPTION

SVDZ24NT is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan new planar VDMOS process. The improved planar stripe cell and the improved guard ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. This device is widely used in electrical ballast, low power switching power supply.



1.Gate 2.Drain 3.Source



TO-220-3L TO-252-2L

FEATURES

- 17A,55V,$R_{DS(on)(typ.)}$=45mΩ@V_{GS}=10V
- Low gate charge
- Low Crss
- Fast switching
- Improved dv/dt capability

ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SVDZ24NT	TO-220-3L	SVDZ24NT	Pb free	Tube
SVDZ24NDTR	TO-252-2L	SVDZ24ND	Halogen free	Tape & Reel

ABSOLUTE MAXIMUM RATINGS (T_C=25°C UNLESS OTHERWISE NOTED)

Characteristics		Symbol	Ratings		Unit
			SVDZ24NT	SVDZ24ND	
Drain-Source Voltage		V_{DS}	55		V
Gate-Source Voltage		V_{GS}	±20		V
Drain Current	T_C=25°C	I_D	17		A
	T_C=100°C		12		
Drain Current Pulsed		I_{DM}	68		A
Power Dissipation(T_C=25°C)		P_D	45	39	W
-Derate above 25°C			0.36	0.3	W/°C
Single Pulsed Avalanche Energy (Note 1)		E_{AS}	122		mJ
Operation Junction Temperature Range		T_J	-55～+175		°C
Storage Temperature Range		T_{stg}	-55～+175		°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings		Unit
		SVDZ24NT	SVDZ24ND	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.78	3.2	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	62	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C UNLESS OTHERWISE NOTED)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	55	--	--	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=55V, V_{GS}=0V	--	--	20	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}= V_{DS}, I_D=250μA	2.0	--	4.0	V
Static Drain-Source On State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=10A	--	45	70	mΩ
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	--	400	--	pF
Output Capacitance	C_{oss}		--	130	--	
Reverse Transfer Capacitance	C_{rss}		--	12.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=28V, V_{GS}=10V, R_G=25Ω, I_D=10A (Note 2,3)	--	5.4	--	ns
Turn-on Rise Time	t_r		--	32.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	22.1	--	
Turn-off Fall Time	t_f		--	12.4	--	
Total Gate Charge	Q_g	V_{DD}=44V, V_{GS}=10V, I_D=10A (Note 2,3)	--	10.5	--	nC
Gate-Source Charge	Q_{gs}		--	2.5	--	
Gate-Drain Charge	Q_{gd}		--	4.0	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	17	A
Pulsed Source Current	I_{SM}		--	--	68	
Diode Forward Voltage	V_{SD}	I_S=10A,V_{GS}=0V	--	--	1.3	V
Reverse Recovery Time	T_{rr}	I_S=10A,V_{GS}=0V, dI_F/dt=100A/μS (Note 2)	--	43	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.05	--	μC

Notes:

1. L=1mH, I_{AS}=13A, V_{DD}=25V, R_G=25Ω, starting T_J=25°C;
2. Pulse Test: Pulse width ≤300μs,Duty cycle≤2%;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

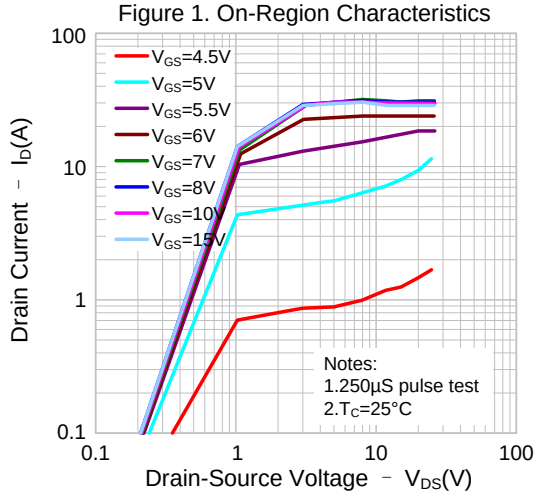


Figure 2. Transfer Characteristics

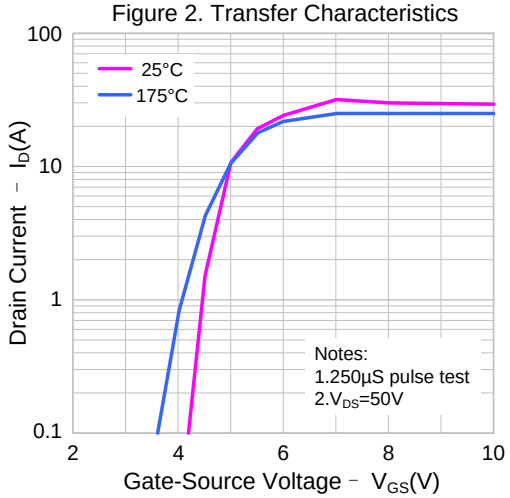


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

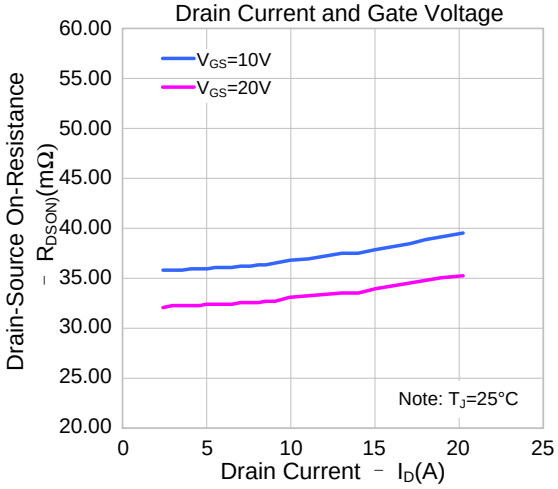


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

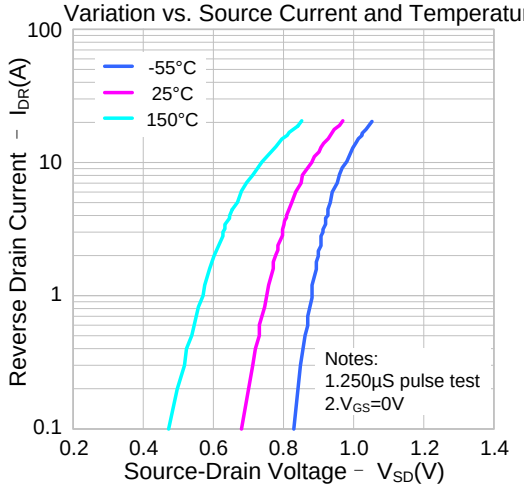


Figure 5. Capacitance Characteristics

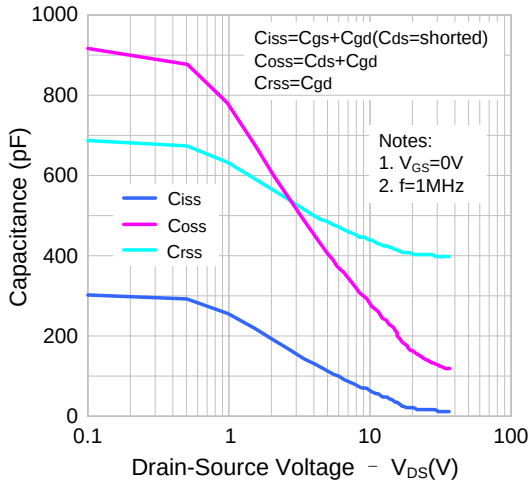
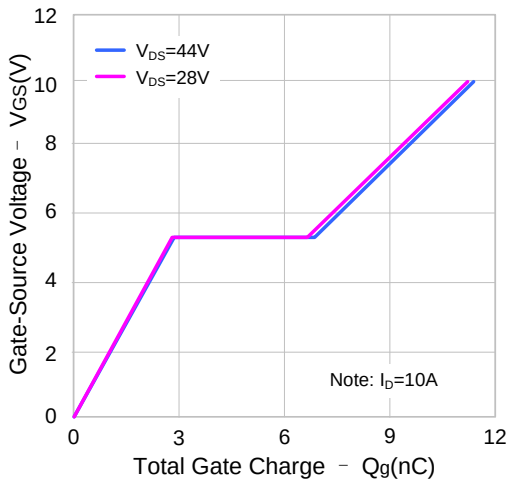


Figure 6. Gate Charge Characteristics



TYPICAL CHARACTERISTICS (CONTINUED)

Figure 7. Breakdown Voltage Variation vs. Temperature

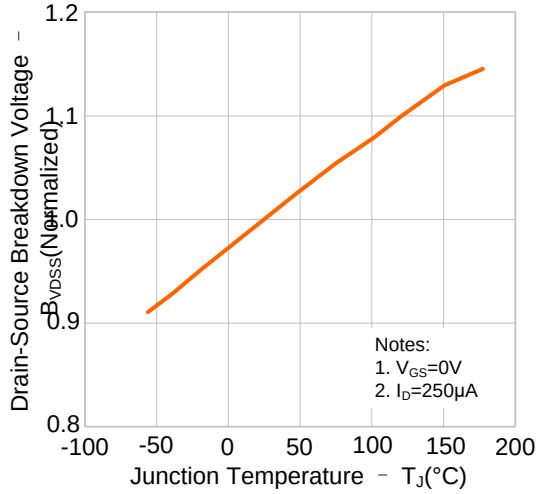


Figure 8. On-resistance Variation vs. Temperature

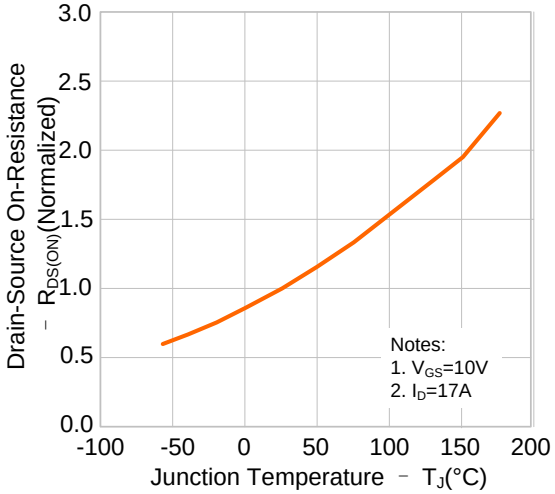


Figure9-1. Max. Safe Operating Area(SVDZ24NT)

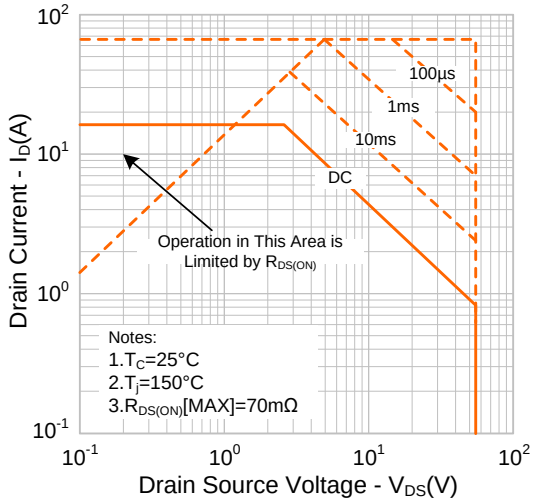


Figure 9-2. Max. Safe Operating Area(SVDZ24ND)

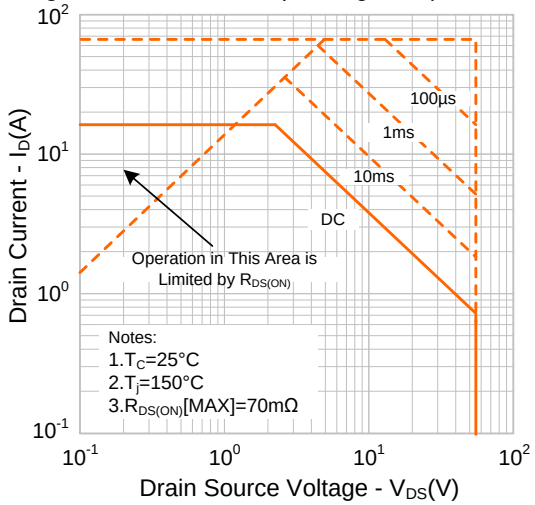
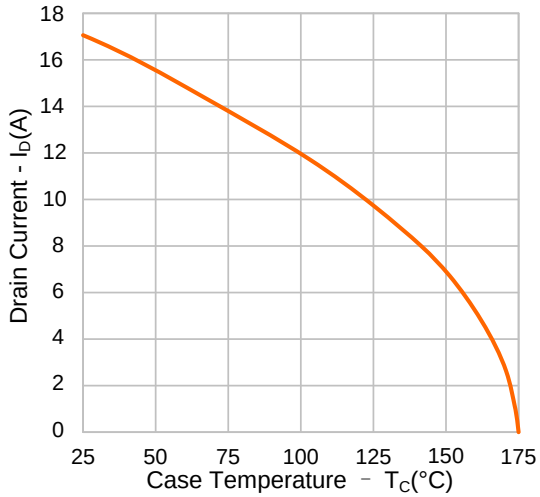
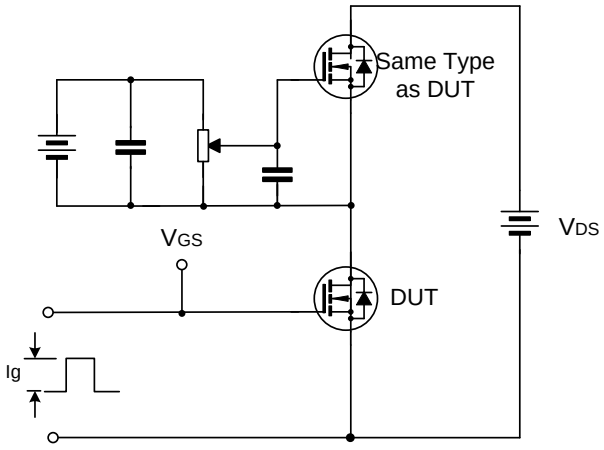


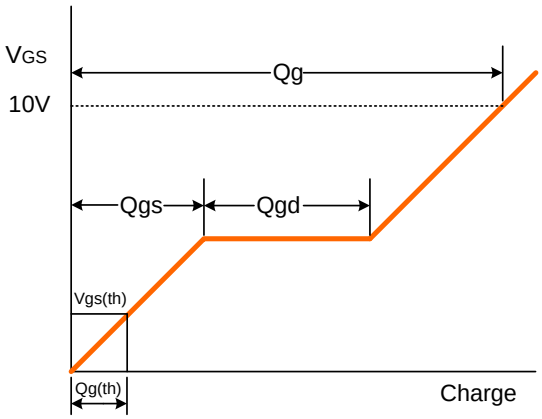
Figure 10. Maximum Drain Current vs. Case Temperature



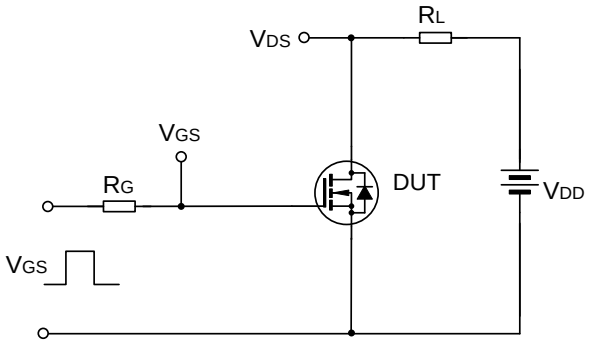
TYPICAL TEST CIRCUIT

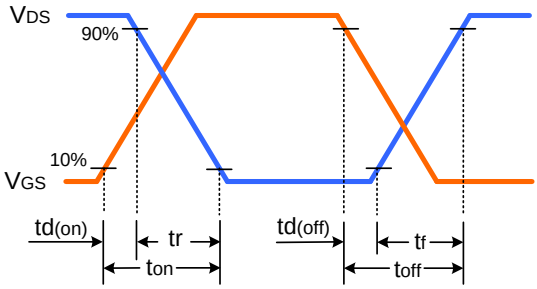
Gate Charge Test Circuit & Waveform



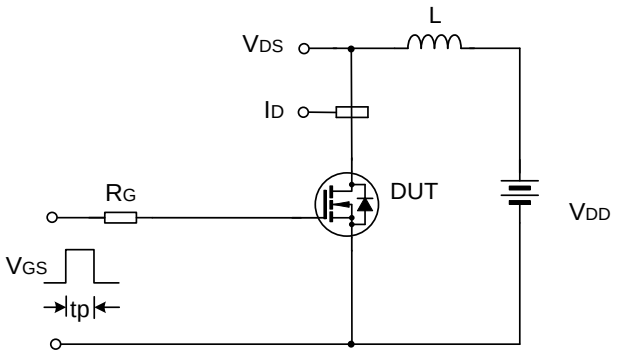


Resistive Switching Test Circuit & Waveform

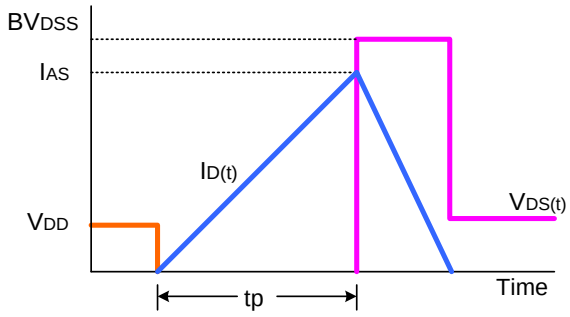




Unclamped Inductive Switching Test Circuit & Waveform



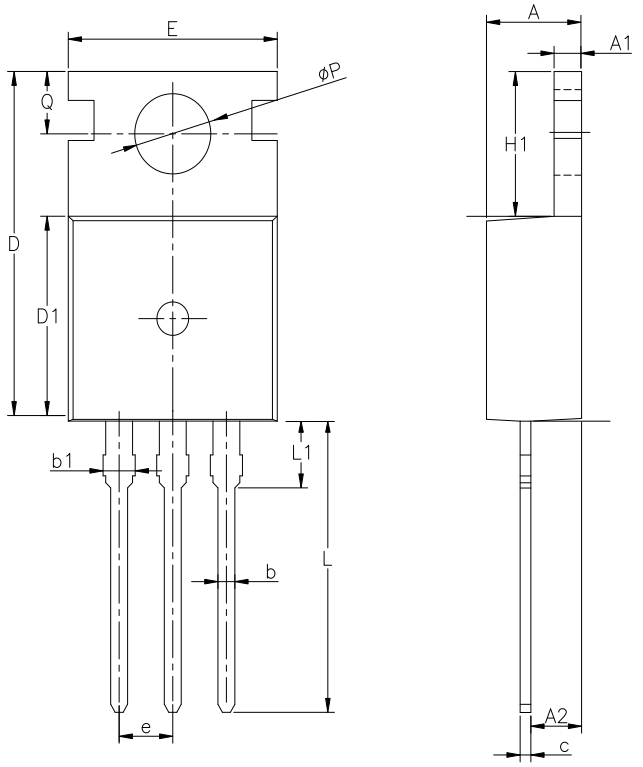
$$E_{AS} = \frac{1}{2} LI_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



PACKAGE OUTLINE

TO-220-3L

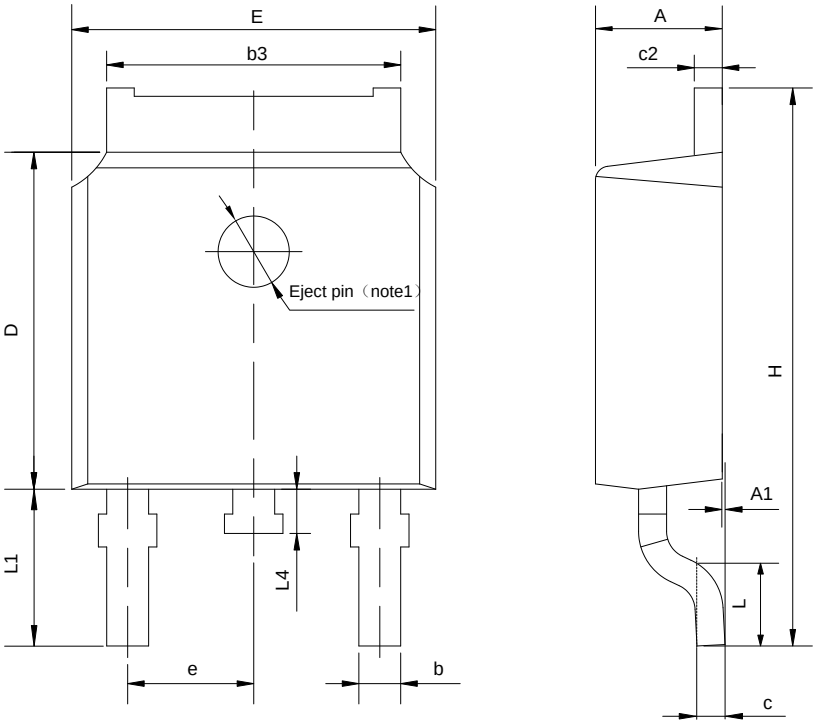
Unit: mm



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.00	1.30	1.50
A2	1.80	2.40	2.80
b	0.60	0.80	1.00
b1	1.00	—	1.60
c	0.30	—	0.70
D	15.10	15.70	16.10
D1	8.10	9.20	10.00
E	9.60	9.90	10.40
e	2.54BSC		
H1	6.10	6.50	7.00
L	12.60	13.08	13.60
L1	—	—	3.95
ϕP	3.40	3.70	3.90
Q	2.60	—	3.20

TO-252-2L

Unit: mm



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.10	2.30	2.50
A1	0	—	0.127
b	0.66	0.76	0.89
b3	5.10	5.33	5.46
c	0.45	—	0.65
c2	0.45	—	0.65
D	5.80	6.10	6.40
E	6.30	6.60	6.90
e	2.30TYP		
H	9.60	10.10	10.60
L	1.40	1.50	1.70
L1	2.90REF		
L4	0.60	0.80	1.00

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Rev.: 1.2

Revision History:

1. Add the package information of TO-252-2L

Rev.: 1.1

Revision History:

1. Modify the package information of TO-220-3L

Rev.: 1.0

Revision History:

1. First release